



HER1001G - HER1008G

10.0AMPS. Glass Passivated High Efficient Rectifiers

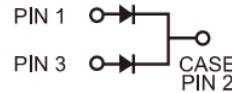
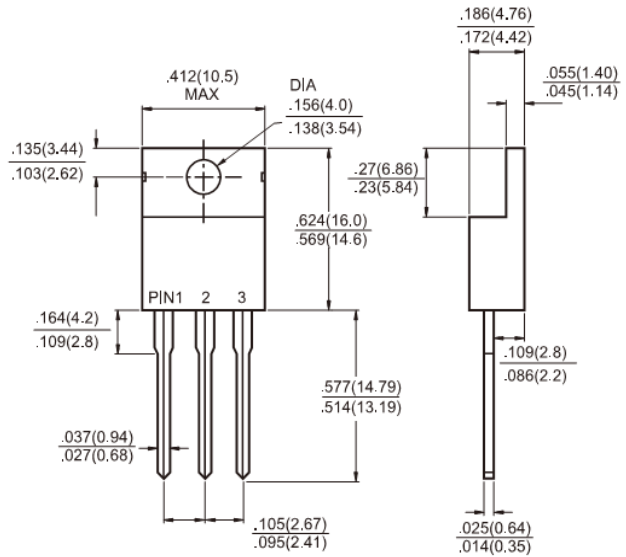
TO-220AB

Features

- ✧ Glass passivated chip junction
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Case: TO-220AB Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering guaranteed: 260°C / 10s / .16", (4.06mm) from case
- ✧ Weight: 2.24 grams



Dimensions in inches and (millimeters)

Marking Diagram



- HER100XG = Specific Device Code
- G = Green Compound
- Y = Year
- WW = Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HER 1001G	HER 1002G	HER 1003G	HER 1004G	HER 1005G	HER 1006G	HER 1007G	HER 1008G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	10								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	125								A
Maximum Instantaneous Forward Voltage (Note 1) @ 5 A	V_F	1.0			1.3		1.7			V
Maximum DC Reverse Current @ $T_A=25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A=125^\circ\text{C}$	I_R	10				400				uA
Maximum Reverse Recovery Time (Note 2)	T_{rr}	50				80				nS
Typical Junction Capacitance (Note 3)	C_j	60				40				pF
Typical Thermal Resistance	$R_{\theta JC}$	1.5								$^\circ\text{C/W}$
Operating Temperature Range	T_J	- 65 to + 150								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 65 to + 150								$^\circ\text{C}$

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $IRR=0.25A$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (HER1001G THRU HER1008G)

FIG. 1- MAXIMUM FORWARD CURRENT DERATING CURVE

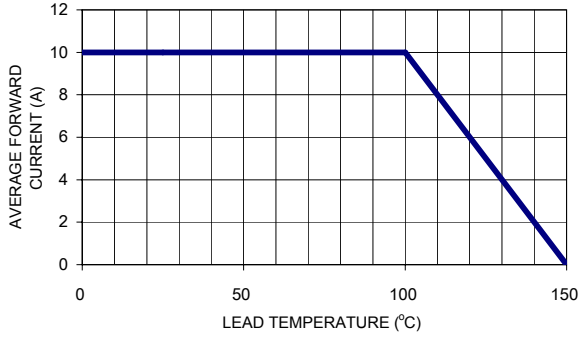


FIG. 2- TYPICAL REVERSE CHARACTERISTICS

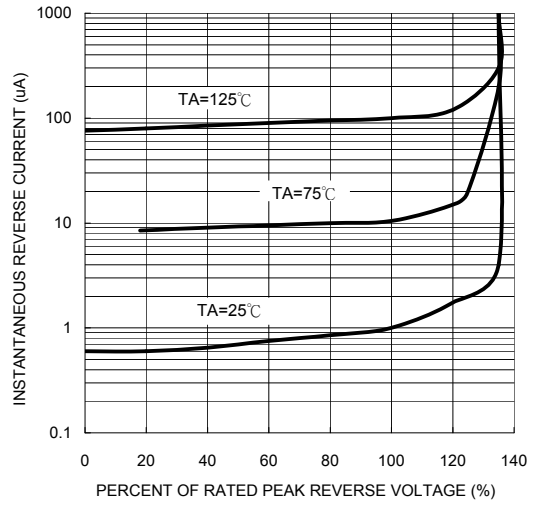


FIG. 3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

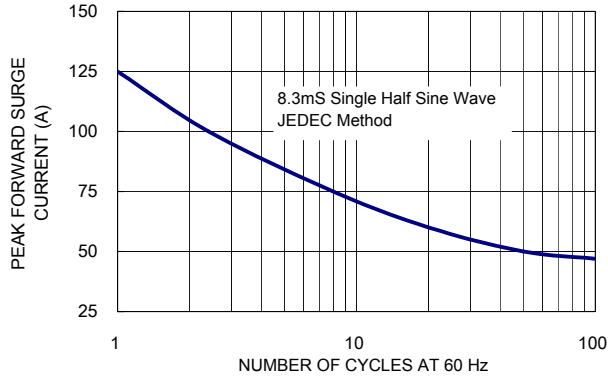


FIG. 5- TYPICAL FORWARD CHARACTERISTICS

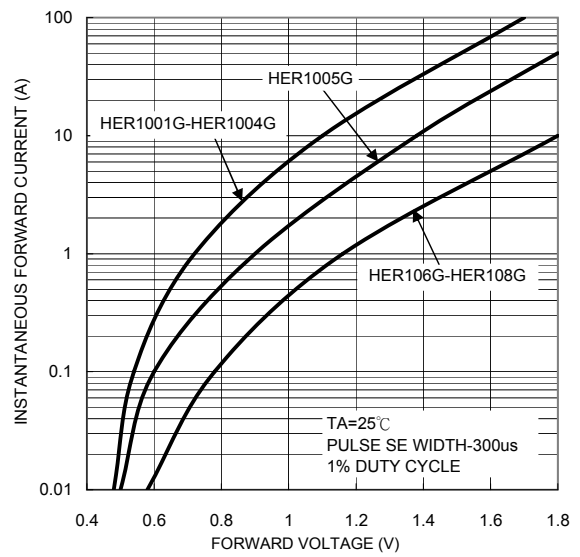


FIG. 4- TYPICAL JUNCTION CAPACITANCE

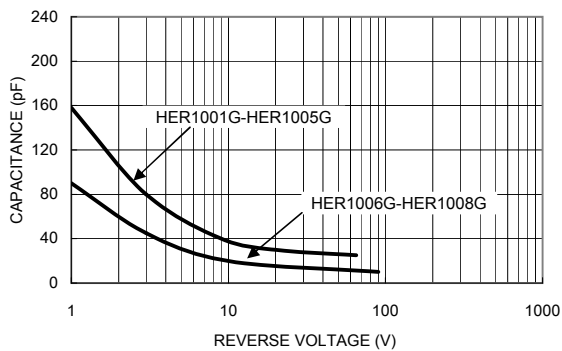


FIG. 6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

